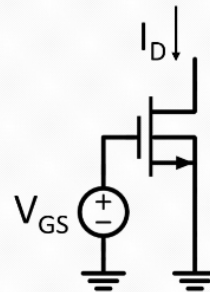
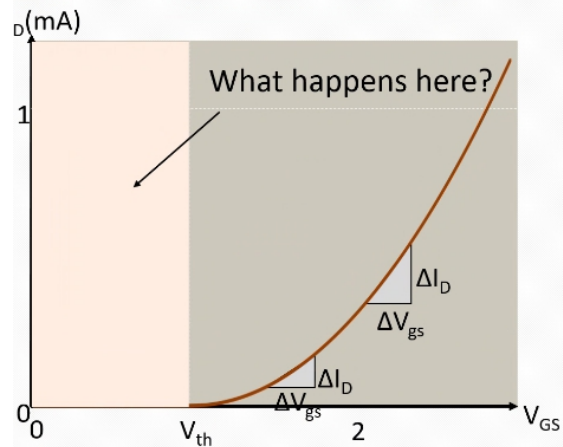


Transconductance



gm

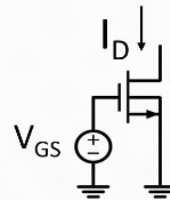
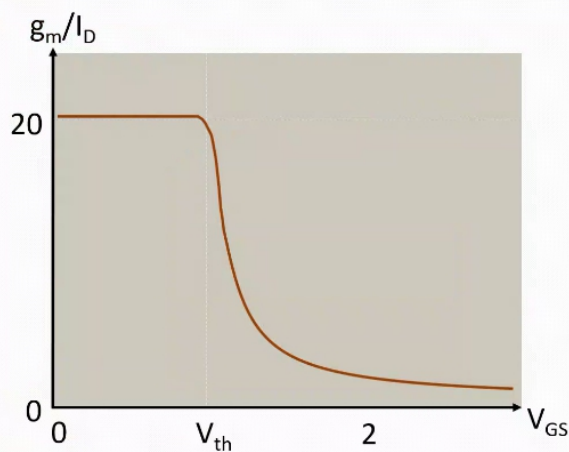
gm/ I_D

f_T

r_{ds}

Adc

gm over I_D



gm

gm/ I_D

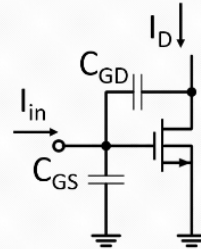
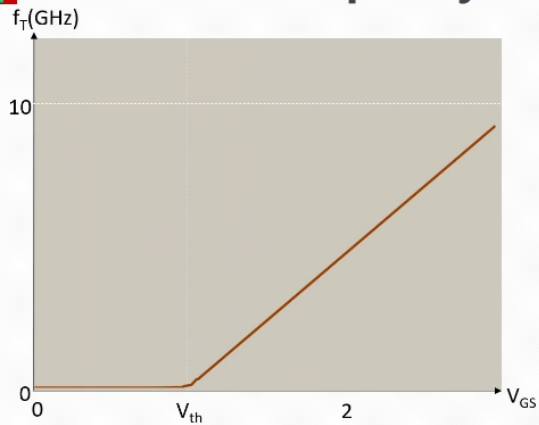
f_T

r_{ds}

Adc

Transconductance efficiency highest in subthreshold

Transition Frequency



gm

gm/I_D

f_T

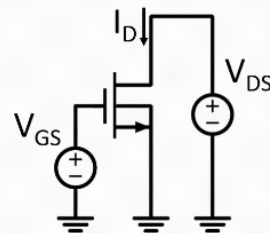
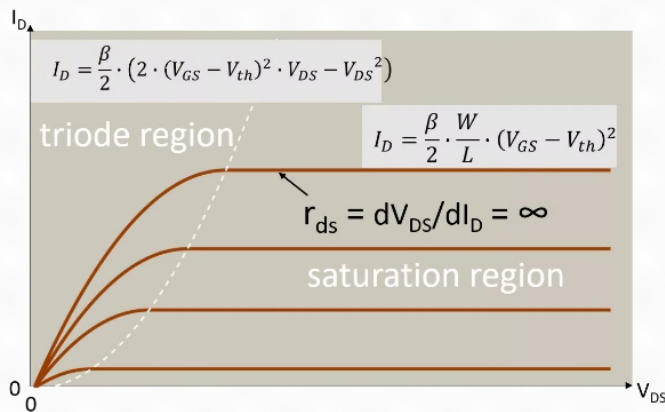
r_{ds}

Adc

$$f_T = \frac{1}{2\pi} \cdot \frac{g_m}{C_{GS} + C_{GD}}$$

f_T is defined as the frequency where $I_D/I_{in} = 1$

Output Resistance



gm

gm/I_D

f_T

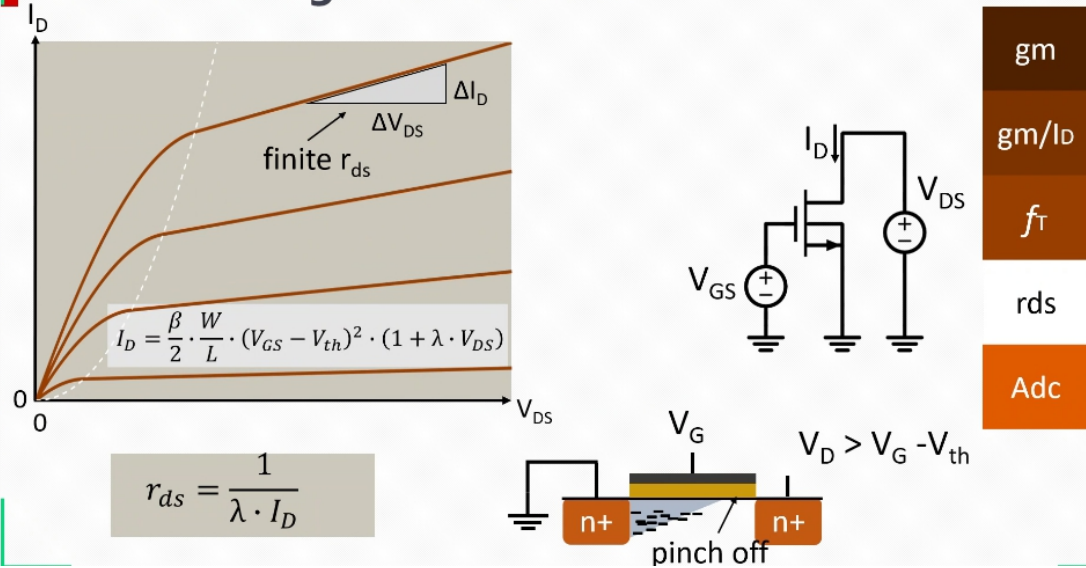
r_{ds}

Adc

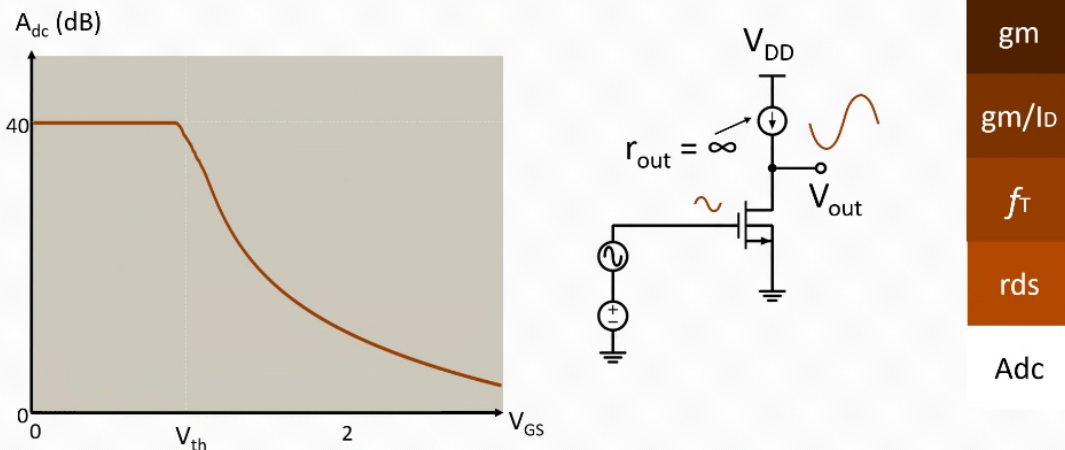
Operate as **switch in triode** for $V_{DS} < V_{GS} - V_{th}$ (V_{ov})

Operate as **amplifier in saturation** for $V_{DS} > V_{GS} - V_{th}$ (V_{ov})

Channel Length Modulation



Intrinsic Gain

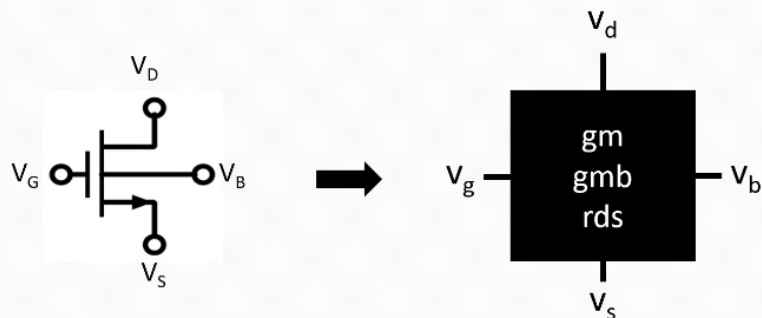


For an ideal current source load the gain is only limited r_{ds} .

➡ The intrinsic DC gain is the highest possible gain we can hope for.

Small Signal Model

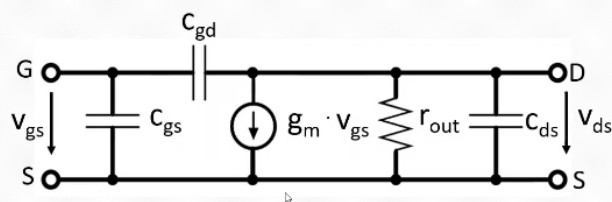
What can we do with these small signal parameters?



They allow us to see the transistor as linearized black box

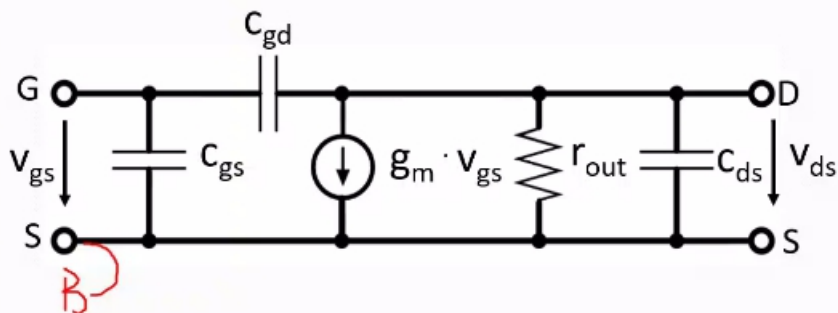
Small Signal Model

Let's look inside the black box:



Also called AC model because it is valid for small variations (AC) around the DC operating point

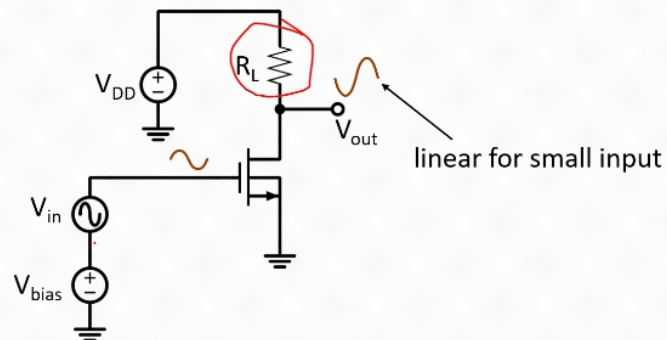
Navigation icons: back, forward, search, etc.



四部分 GDSB

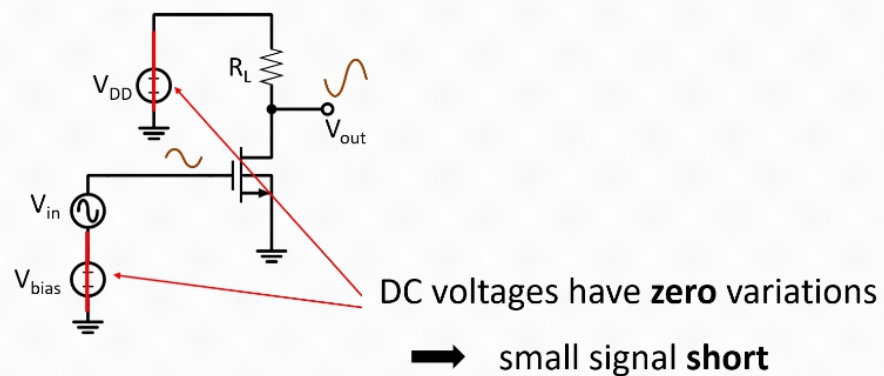
Small Signal Model

Example of an amplifier:



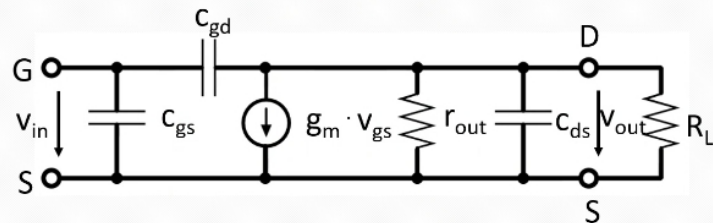
Small Signal Model

Example of an amplifier:



Small Signal Model

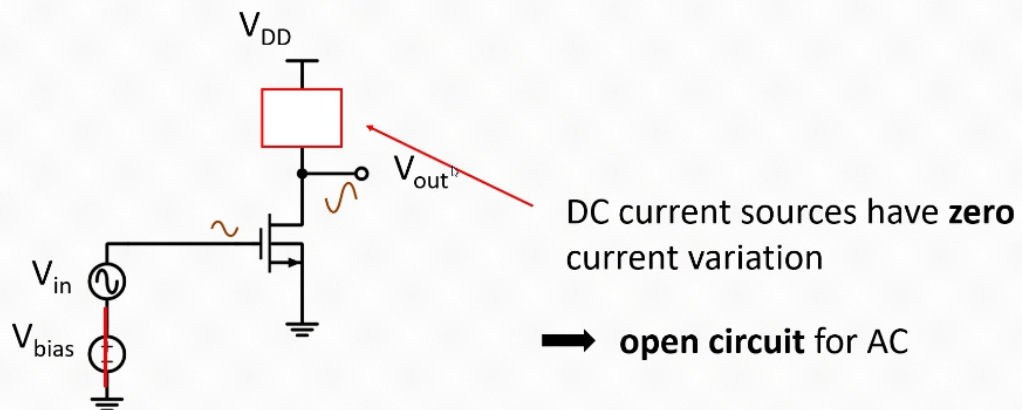
Let's derive the small signal model for this amplifier:



$$\frac{v_{out}}{v_{in}} = -g_m(r_{out} || R)$$

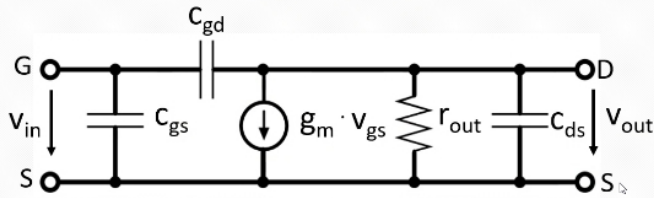
Small Signal Model

A better amplifier:



Small Signal Model

Let's derive the small signal model for this amplifier:

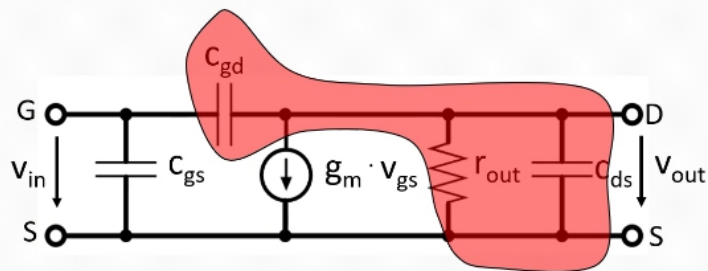


$$\frac{v_{out}}{v_{in}} = -g_m r_{out}$$

➡ Current source loading gives intrinsic gain.

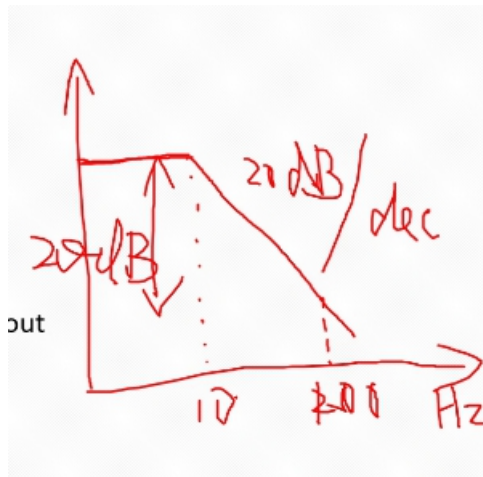
Small Signal Model

What about the capacitances?



$$\frac{v_{out}}{v_{in}} = -g_m r_{out} \frac{1 - sC_{gd}/g_m}{1 + s(C_{gd} + C_{ds})r_{out}}$$

经过一个极点会下降 20dB



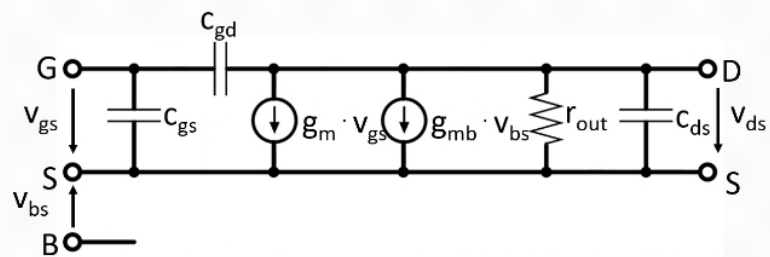
Ads 是幅度频谱的纵坐标

Small Signal Model

What about the bulk?

$$V_{bs} \uparrow \rightarrow V_{th} \downarrow \rightarrow I_{ds} \uparrow$$

→ Can be modelled as transconductance g_{mb}



I_{ds} 与 $(V_{gs} - V_{th})$ 有关

注意 V_{bs} 是正是负，还是 0